PTO/SB/08A (08-03)
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Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	10/654189
Filing Date	Sept 3, 2003
First Named Inventor	Ashton et al
Art Unit	~~2824~~ 2891
Examiner Name	Wilson, Christian D.
Attorney Docket Number	100201669-1

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
CDW	1	US- 2002/0176349	11/28/2002	Gibson et al	
	2	US- 2004/0086802	5/6/2004	Gibson	
	3	US- 3983542	9/28/1976	Ovshinsky	
	4	US- 2003/0081527	5/1/2003	Gibson et al	
CDW	5	US- 5557596	9/17/1996	Gibson et al	
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Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3]-Number[4]-Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T[6]

Examiner Signature	Christian Wilson	Date Considered	3/23/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. [1]Applicant's unique citation designation number (optional). [2]See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached.

FORM PTO-1449	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	100201669-1	10/654189	
(Use several sheets if necessary)	APPLICANT: Ashton, et al		
	FILING DATE: Sept. 3, 2003	GROUP: ~~2129~~ 2829	

REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
CDW	1A	5,557,596	09/17/96	Gibson et al	
CDW	1B	6,256,224	07/03/01	Perner, et al.	
CDW	1C	6,262,421	07/17/01	Tran	
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	1L					
	1M					
	1N					
	1O					
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

CDW	1Q	Kampmann, et al. A Cadmium-free CuInSe2 Superstrate Solar Cell Fabricated by Electrodeposition Using a ITO/In2Se3/CuInSe2/Au Structure; Progress in Photovoltaics; (1999) pgs. 129-135.
	1R	Rechid, et al. Characterising Superstrate CIS solar cells with electron beam induced current; Thin Solid Films; (2000) pgs. 361-362.
CDW	1S	Ward, et al. Cu(In,Ga)Se2 Thin-Film Concentrator Solar Cells; NCPV Program Review Meeting; 10/01.

EXAMINER	DATE CONSIDERED
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CW	2Q	Scofield, et al. Sputtered molybdenum bilayer back contact for copper indium diselenide-based polycrystalline thin-film solar cells; Thin Solid Films (1995) pgs. 26-31
	2R	Gabor, et al. High-efficiency CuInxGa1-xSe2 solar cells made from (Inx,Ga1-x)2Se3 precursor films; American Institute of Physics, (1994) pgs. 198-200
CW	2S	Nakayama, et al. AES, LEELS and XPS studies on the interface formation between layered semiconductors GaSe and InSe; Surface Science (1991)

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OK	3Q	Nishida, et al. Single-beam overwrite experiment using In-Se based phase-change optical media; American Insitute of Physics (1987) pgs. 667-669
	3R	Sanchez-Royo, et al. Optical and photovoltaic properties of indium selenide thin films prepared by van der Waals epitaxy; Journal of Applied Physics (2001) pgs. 2818-2823
OK	3S	Otsmane, et al. Epitaxy of layered semiconductor thin films; Applied Surface Science (1993) pgs. 479-481

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	4Q	Emery, et al. Reflection high-energy electron diffraction studies of InSe and GaSe layered compounds grown by molecular beam epitaxy; Journal of Applied Physics (1992) pgs. 3256-3259
	4R	Tatsuyama, et al. Heteroepitaxy between layered semiconductors GaSe and InSe; Applied Surface Science (1989) pgs. 539-543
	4S	Gashimzade, et al. Eneregy spectrum and effective mass of carriers in the InSe/GaSe superlattice; Z. Physics (1996) pgs. 219-222

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Christine Wilson	3/23/05

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GW	5Q	Shigetomi, et al. Electrical and photovoltaic properties of Cu-doped p-GaSe/n-InSe heterojunction; Journal of Applied Physics; (2000); pgs. 1520-1524
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